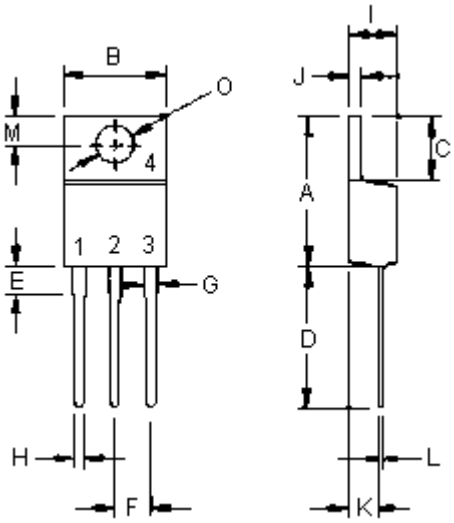
PNP Power Transistor

Complementary Silicon Plastic Power Transistors

Features:

Designed for use in general purpose power amplifier and switching applications.

- Collector-emitter sustaining voltage-$V_{CEO\ (sus)}$ = 100V (minimum).
- Collector-emitter saturation voltage-$V_{CE\ (sat)}$ = 1.5V (maximum) at I_C = 6.0A.
- Current gain-bandwidth product f_T = 3.0 MHz (minimum) at I_C = 500mA.



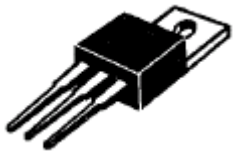
Pin 1. Base.
2. Collector.
3. Emitter.
4. Collector (Case).

Dimensions	Minimum	Maximum
A	14.68	15.31
B	9.78	10.42
C	5.01	6.52
D	13.06	14.62
E	3.57	4.07
F	2.42	3.66
G	1.12	1.36
H	0.72	0.96
I	4.22	4.98
J	1.14	1.38
K	2.20	2.97
L	0.33	0.55
M	2.48	2.98
O	3.70	3.90

Dimensions : Millimetres

PNP
TIP42C

6 Ampere
Complementary Silicon
Power Transistors
40 to 100 Volts
65 Watts



TO-220

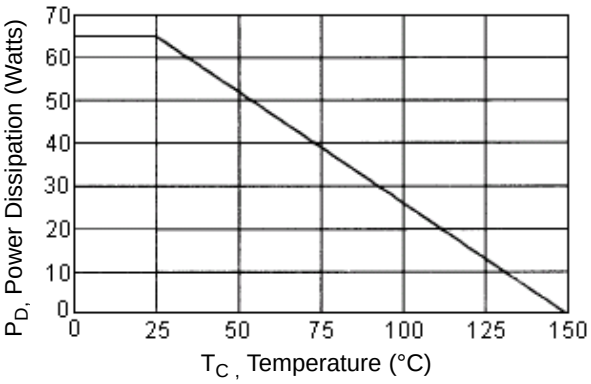
Maximum Ratings

Characteristic	Symbol	TIP42C	Unit
Collector-Emitter Voltage	V_{CEO}	100	V
Collector-Base Voltage	V_{CBO}		
Emitter-Base Voltage	V_{EBO}	5	
Collector Current - Continuous - Peak	I_C	6 10	A
Base Current	I_B	2	
Total Power Dissipation at T_C = 25°C Derate above 25°C	P_D	65 0.52	W W/°C
Operating and Storage Junction Temperature Range	T_J, T_{STG}	-65 to +150	°C

Thermal Characteristics

Characteristic	Symbol	Maximum	Unit
Thermal Resistance Junction to Case	Rθjc	1.92	°C/W

Power Derating

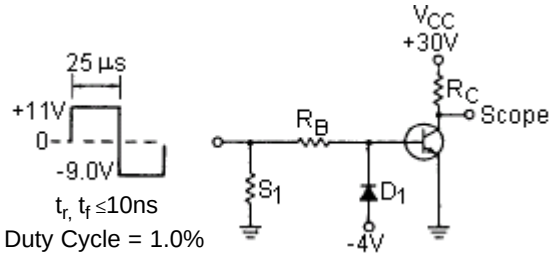


Electric Characteristics (T_C = 25°C unless otherwise noted)

Characteristics	Symbol	Minimum	Maximum	Units
Off Characteristics				
Collector-Emitter Sustaining Voltage (1) (I_C = 30mA, I_B = 0)	$V_{CEO\ (sus)}$	100	-	V
Collector Cut-off Current (V_{CE} = 60V, I_B = 0)	I_{CEO}	-	0.7	mA
Collector Cut-off Current (V_{CE} = 100V, V_{EB} = 0)	I_{CES}	-	0.4	
Emitter Cut-off Current (V_{EB} = 5.0V, I_C = 0)	I_{EBO}	-	1.0	
On Characteristics (1)				
DC Current Gain (I_C = 0.3A, V_{CE} = 4.0V) (I_C = 0.3A, V_{CE} = 4.0V)	h_{FE}	30 15	75	-
Collector-Emitter Saturation Voltage (I_C = 6.0A, I_B = 600mA)	$V_{CE\ (sat)}$	-	1.5	V
Base-Emitter on Voltage (I_C = 6.0A, V_{CE} = 4.0V)	$V_{BE\ (on)}$	-	2.0	
Dynamic Characteristics				
Current Gain-Bandwidth Product (2) (I_C = 500mA, V_{CE} = 10V, f_{TEST} = 1MHz)	f_T	3.0	-	MHz
Small Signal Current Gain (I_C = 500mA, V_{CE} = 10V, f = 1kHz)	h_{fe}	20	-	-

(1) Pulse Test: Pulse Width ≤ 300µs, Duty Cycle ≤ 2.0%.
(2) $f_T = |h_{fe}| \bullet f_{TEST}$

Switching Time Test Circuit

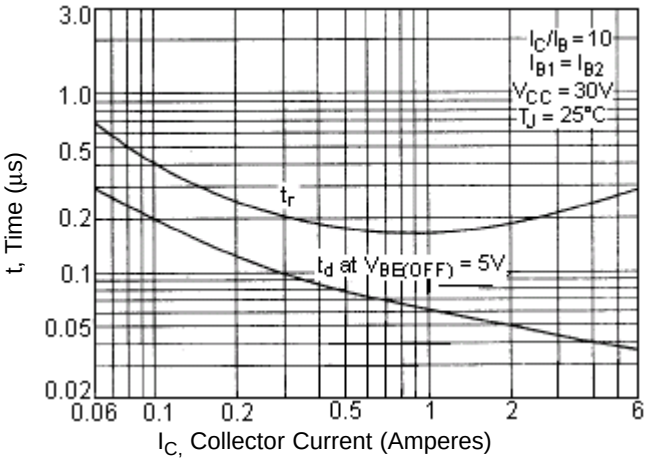


Duty Cycle = 1.0%

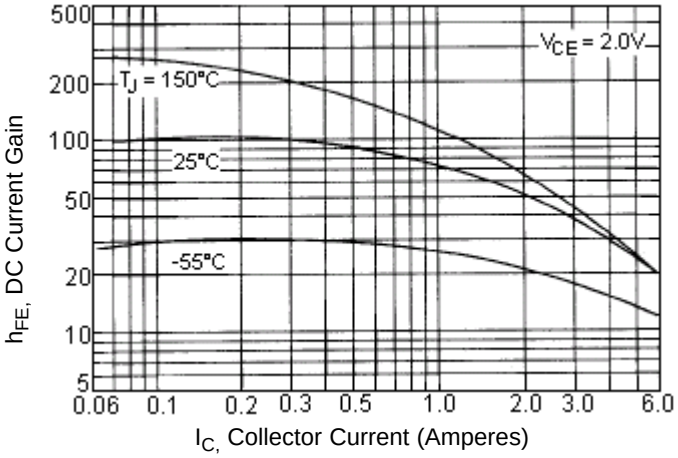
R_B and R_C Varied to Obtain Desired Current Levels

D1 Must be Fast Recovery Type. eg:
MBD5000 used Above I_B = 100mA
MSD6100 used Below I_S = 100mA

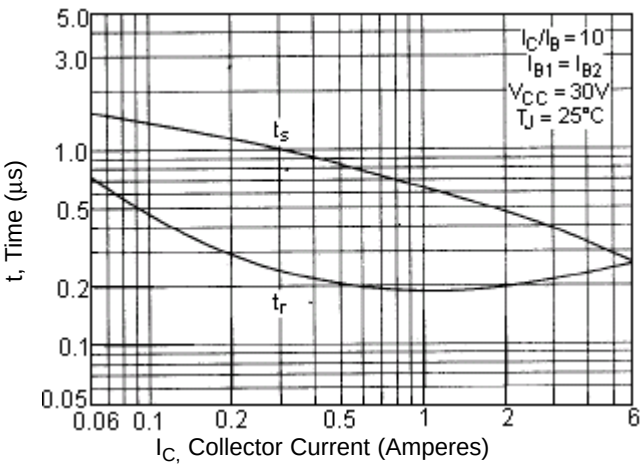
Turn-on Time



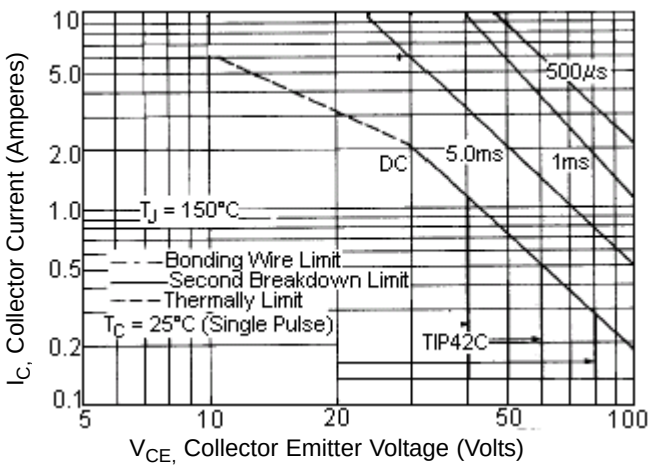
DC Current Gain



Turn-off Time



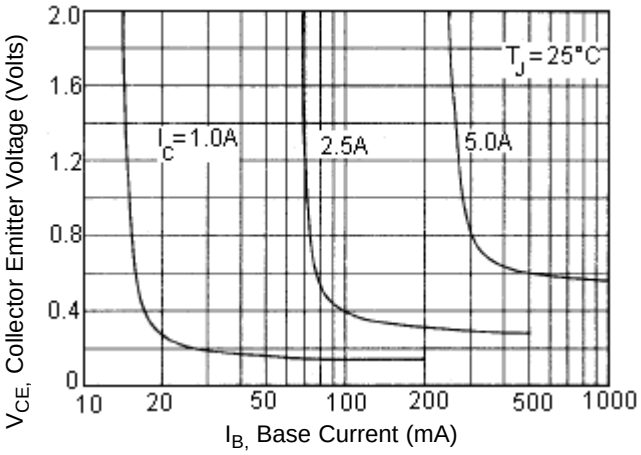
Active Region Safe Operating Area



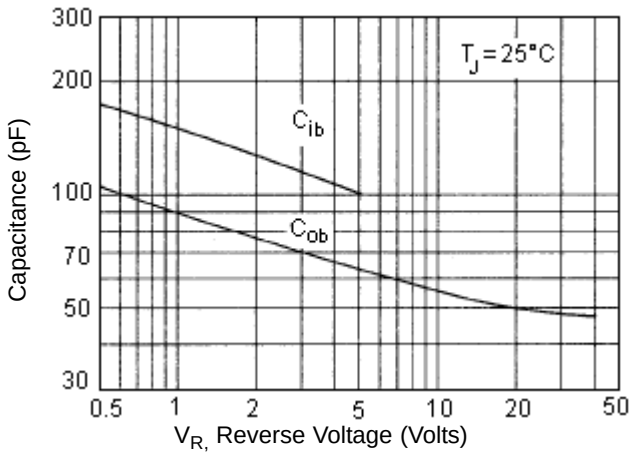
PNP Power Transistor

There are two limitation on the power handling ability of a transistor: average junction temperature and second breakdown safe operating area curves indicate I_C-V_{CE} limits of the transistor that must be observed for reliable operation i.e. the transistor must not be subjected to greater dissipation than curves indicate.
The data of curve is base on $T_{J\,(PK)}$ = 150°C; T_C is variable depending on power level. Second breakdown pulse limits are valid for duty cycles to 10% provided $T_{J\,(PK)} \leq$150°C, At high case temperatures, thermal limitation will reduce the power that can be handled to values less than the limitations imposed by second breakdown.

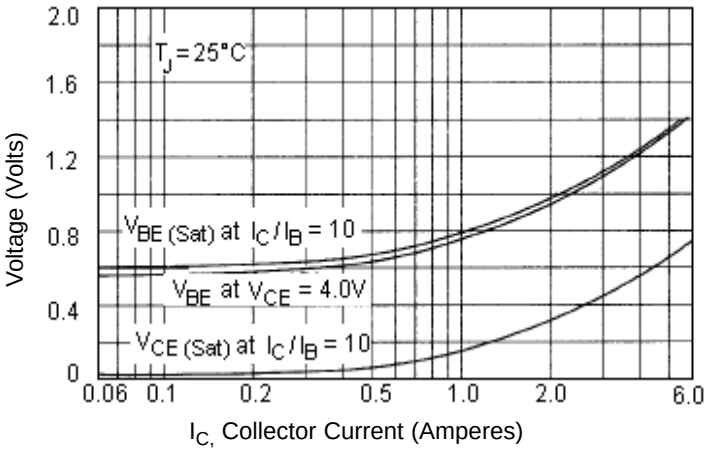
Collector Saturation Region



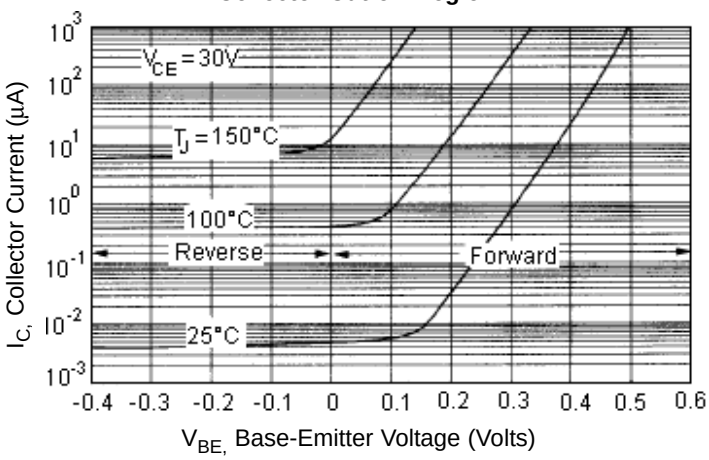
Capacitances



"ON" Voltage



Collector Cut-off Region



Part Number Table

Description	Part Number
PNP Power Transistor	TIP42C